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Kind regards,

Team Nexperia

BC847QAPN

45 V, 100 mA NPN/PNP general-purpose transistor

8 July 2015 **Product data sheet**

1. General description

NPN/PNP general-purpose transistor in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified
- Low package height of 0.37 mm

3. Applications

- General-purpose switching and amplification
- Mobile applications

4. Quick reference data

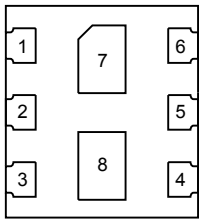
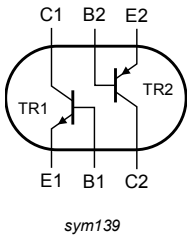
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
V_{CEO}	collector-emitter voltage	open base		-	-	45	V
I_C	collector current			-	-	100	mA
Per transistor; for the PNP transistor with negative polarity							
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 2 mA; T_{amb} = 25 °C		200	-	450	

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	 Transparent top view **DFN1010B-6 (SOT1216)**	 *sym139*
2	B1	base TR1		
3	C2	collector TR2		
4	E2	emitter TR2		
5	B2	base TR2		
6	C1	collector TR1		
7	C1	collector TR1		
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC847QAPN	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216

7. Marking

Table 4. Marking codes

Type number	Marking code
BC847QAPN	01 00 00

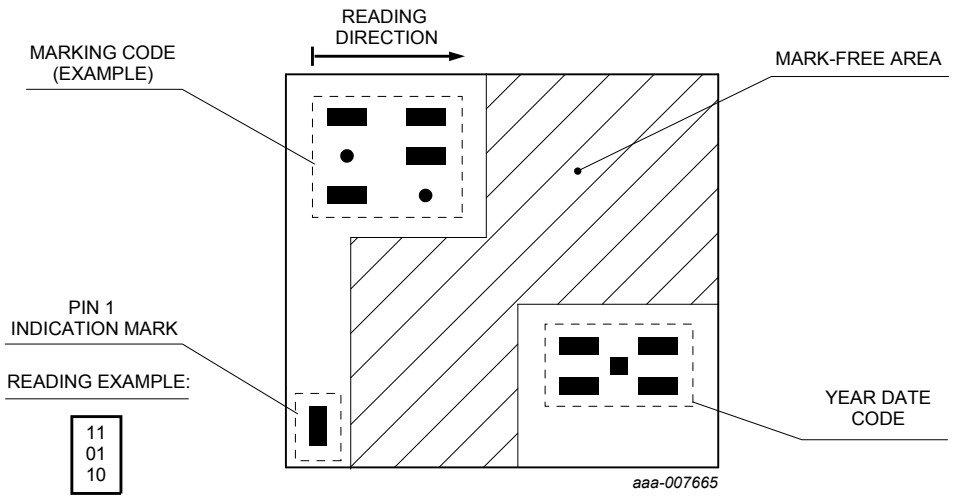


Fig. 1. DFN1010B-6 (SOT1216) binary marking code description

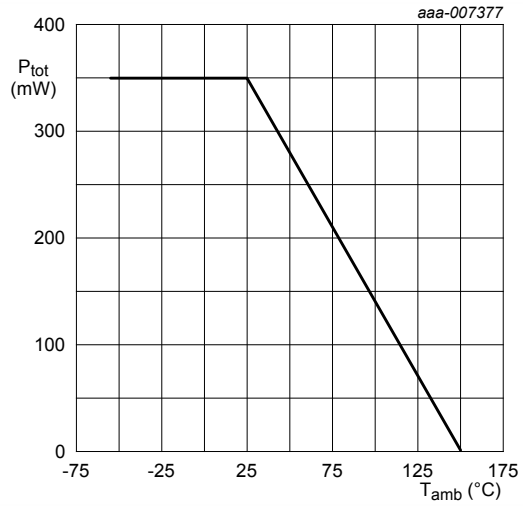
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	45	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
I_C	collector current			-	100	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	200	mA
I_{BM}	peak base current			-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	230	mW
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	350	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

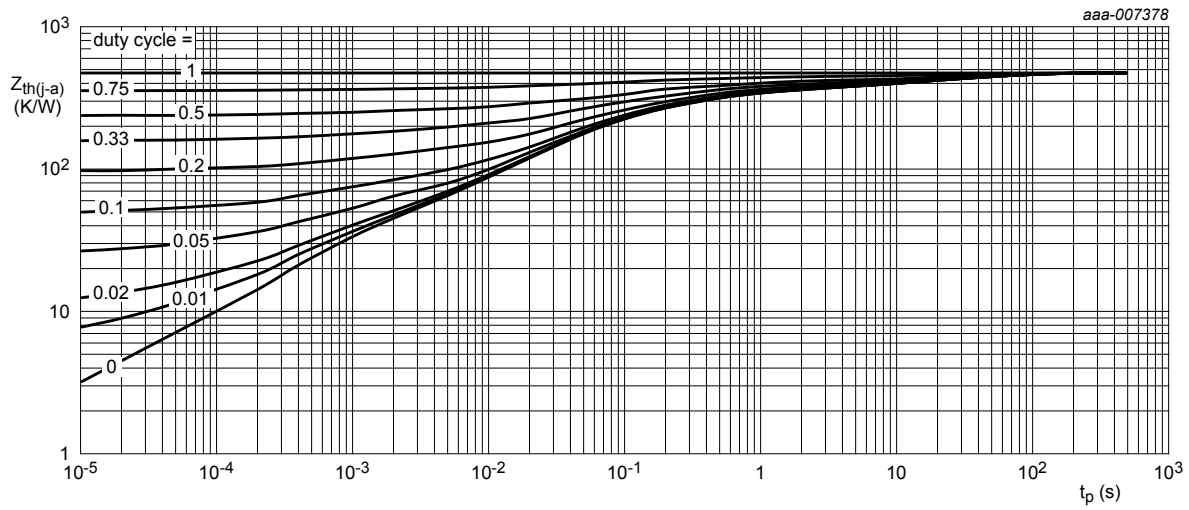
Fig. 2. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



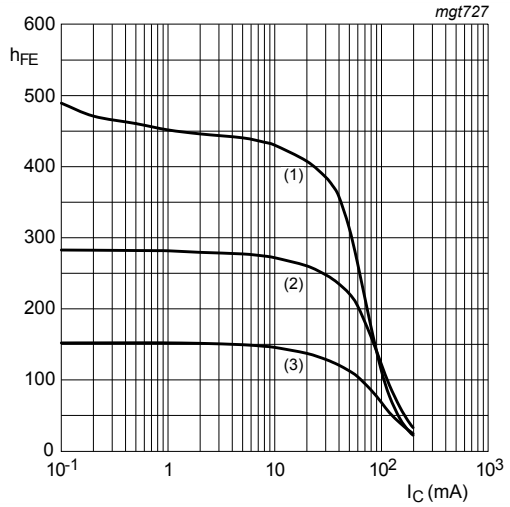
FR4 PCB, standard footprint

Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
I_{CBO}	collector-base cut-off current	V_{CB} = 30 V; I_E = 0 A; T_{amb} = 25 °C		-	-	15	nA
		V_{CB} = 30 V; I_E = 0 A; T_j = 150 °C		-	-	5	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I_C = 0 A; T_{amb} = 25 °C		-	-	100	nA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 2 mA; T_{amb} = 25 °C		200	-	450	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C		-	-	100	mV
		I_C = 100 mA; I_B = 5 mA; pulsed; $t_p \leq 300$ µs; $\delta \leq 0.02$; T_{amb} = 25 °C		-	-	300	mV
V_{BEsat}	base-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C		-	760	-	mV
		I_C = 100 mA; I_B = 5 mA; pulsed; $t_p \leq 300$ µs; $\delta \leq 0.02$; T_{amb} = 25 °C		-	900	-	mV
V_{BE}	base-emitter voltage	V_{CE} = 5 V; I_C = 2 mA; T_{amb} = 25 °C		600	660	725	mV
		V_{CE} = 5 V; I_C = 10 mA; T_{amb} = 25 °C		-	710	820	mV
C_c	collector capacitance	V_{CB} = 10 V; I_E = 0 A; i_e = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	4	pF
f_T	transition frequency	V_{CE} = 5 V; I_C = 10 mA; f = 100 MHz; T_{amb} = 25 °C		100	-	-	MHz
NF	noise figure	V_{CE} = 5 V; I_C = 0.2 mA; R_S = 2 kΩ; f = 1 MHz; B = 200 Hz; T_{amb} = 25 °C		-	-	10	dB
TR1 (NPN)							
C_e	emitter capacitance	V_{EB} = 0.5 V; I_C = 0 A; i_c = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	11	-	pF
TR2 (PNP)							
C_e	emitter capacitance	V_{EB} = -0.5 V; I_C = 0 A; i_c = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	10	-	pF



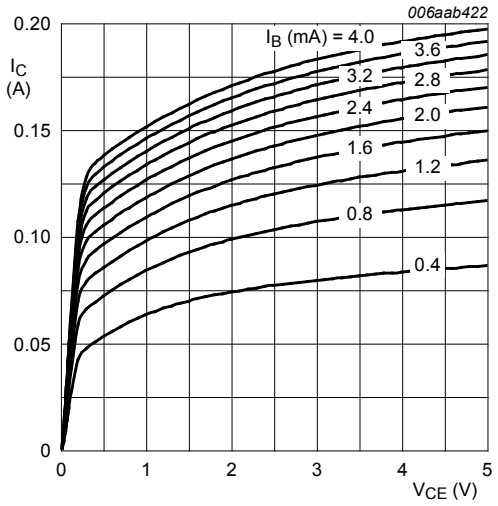
V_{CE} = 5 V

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

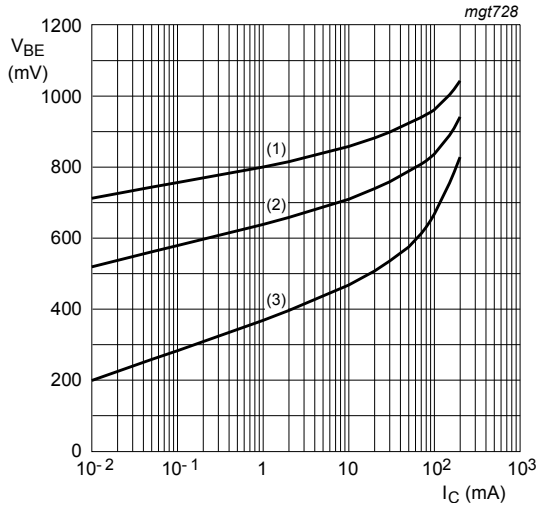
(3) T_{amb} = −55 °C

Fig. 4. NPN transistor: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 5. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



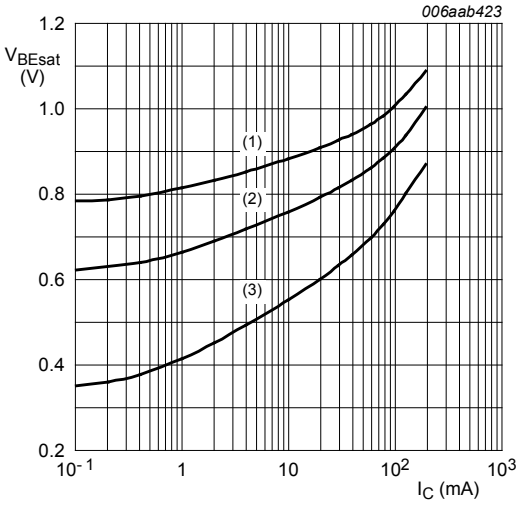
V_{CE} = 5 V

(1) T_{amb} = -55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig. 6. NPN transistor: Base-emitter voltage as a function of collector current; typical values



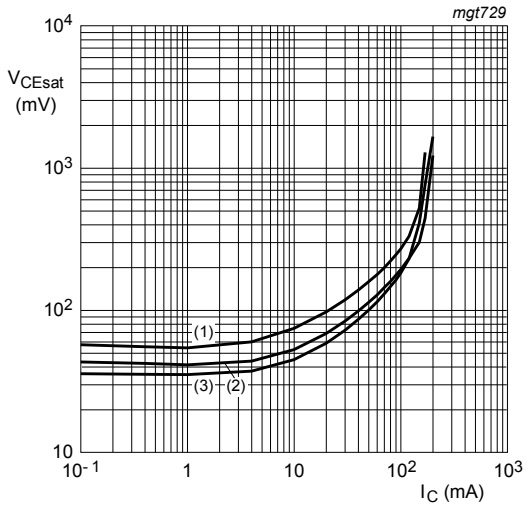
I_C/I_B = 20

(1) T_{amb} = -55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 150 °C

Fig. 7. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



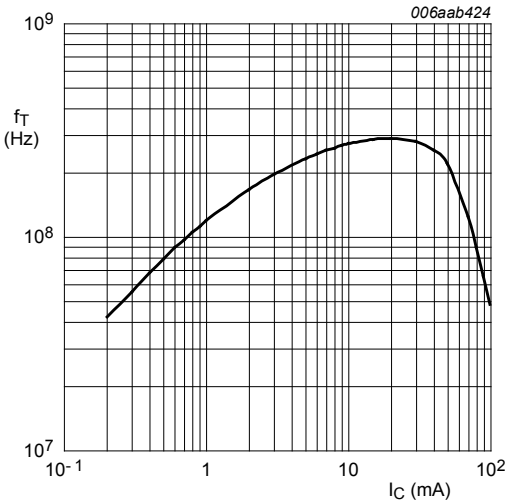
I_C/I_B = 20

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = -55 °C

Fig. 8. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values

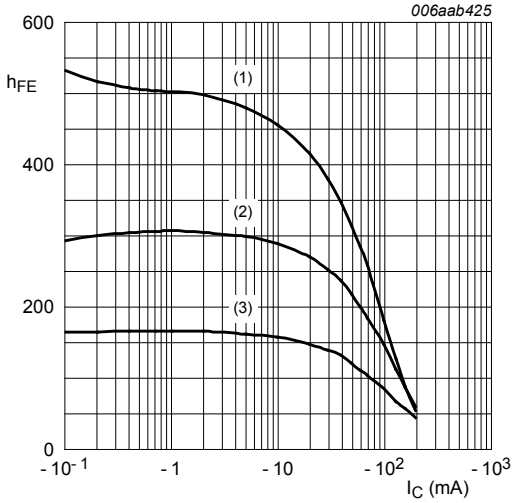


T_{amb} = 25 °C;

V_{CE} = 5 V;

f = 100 MHz

Fig. 9. Transition frequency as a function of collector current; typical values



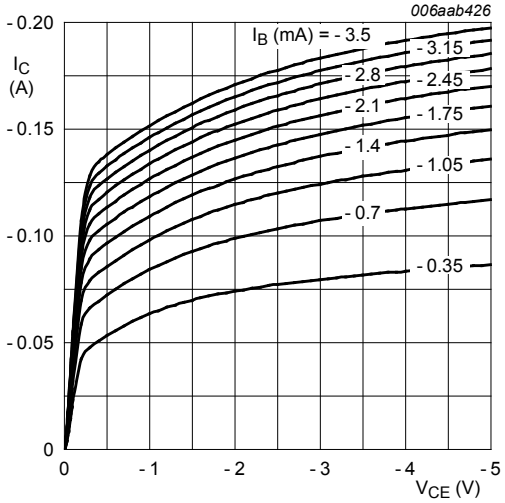
V_{CE} = -5 V

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

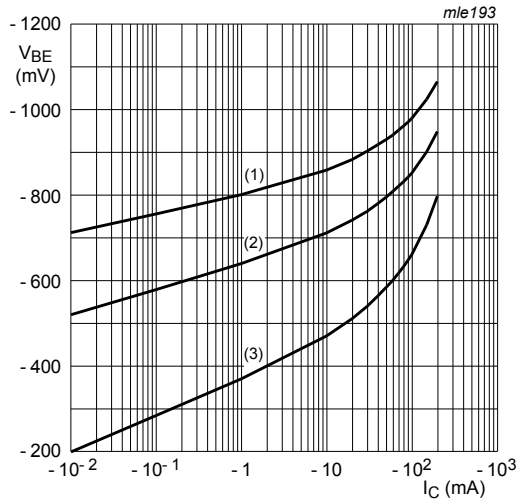
(3) T_{amb} = −55 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



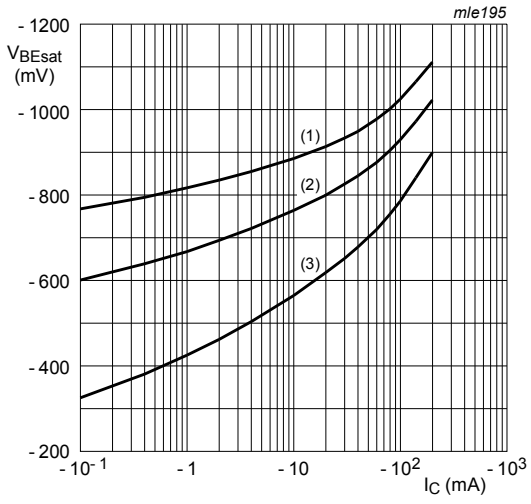
T_{amb} = 25 °C

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



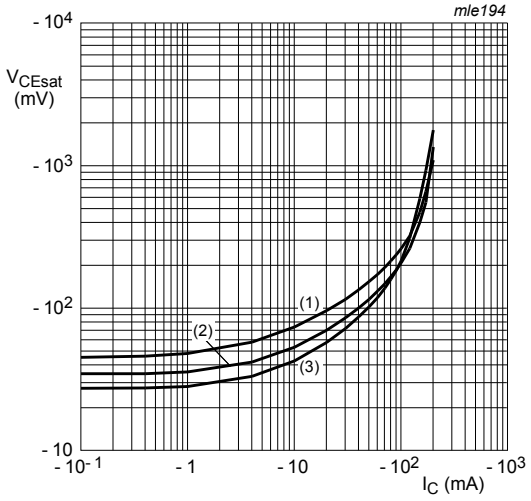
V_{CE} = -5 V
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Fig. 12. PNP transistor: Base-emitter voltage as a function of collector current; typical values



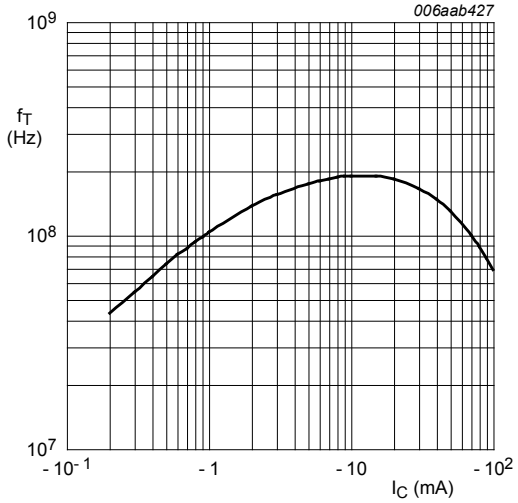
I_C/I_B = 20
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



I_C/I_B = 20
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Fig. 14. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



T_{amb} = 25 °C;
V_{CE} = -5 V;
f = 100 MHz

Fig. 15. PNP transistor: Transition frequency as a function of collector current; typical values

11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

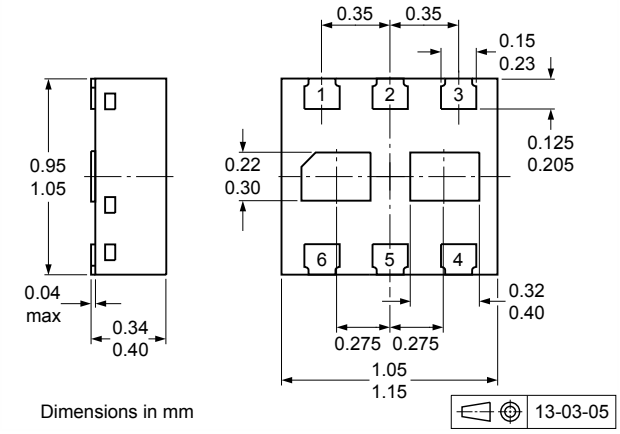


Fig. 16. Package outline DFN1010B-6 (SOT1216)

13. Soldering

Footprint information for reflow soldering of DFN1010B-6 package **SOT1216**

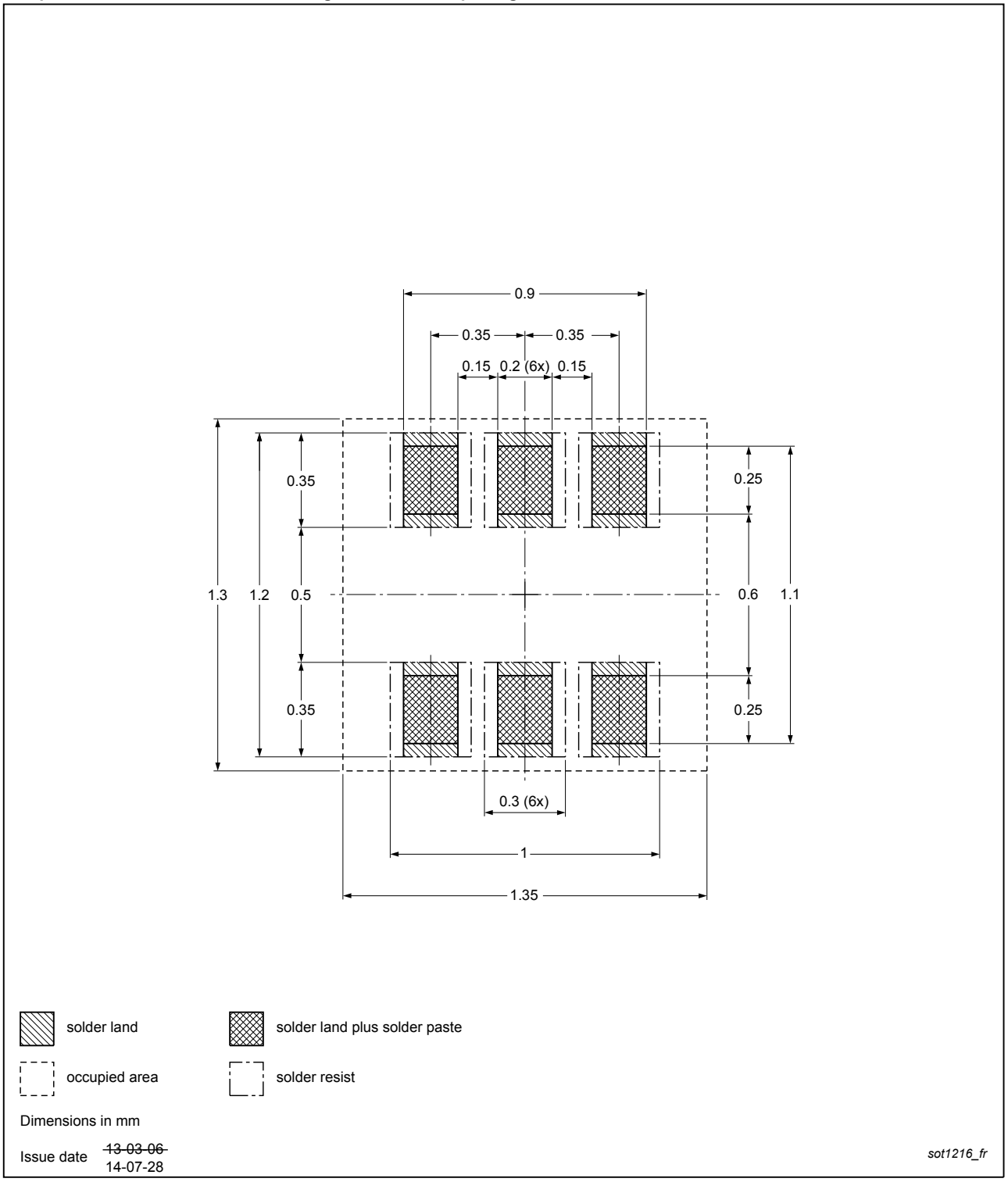


Fig. 17. Reflow soldering footprint for DFN1010B-6 (SOT1216)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC847QAPN v.2	20150708	Product data sheet	-	BC847QAPN v.1
Modification:	• Change of binary marking code position.			
BC847QAPN v.1	20130718	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 8 July 2015